## **FEATURES**

The MBRD540 \_ MBRD5200 is available in TO-252 Package

- Schottky Barrier Chip
- Low forward voltage drops
- Low power loss, high efficiency
- High surge current capability
- High temperature soldering guaranteed

# **MECHANICAL DATA**

Case: DPAK/ TO-252

• Weight: 0.3 grams (approx.)

Mounting Position: Any

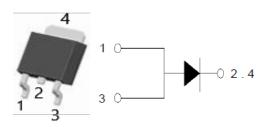
Terminals: Plated Leads Solderable per

MIL-STD-202, Method208.

## **ORDERING INFORMATION**

Package Type	Part Number			
TO-252	MBRD540			
	MBRD545			
	MBRD560			
	MBRD5100			
	MBRD5150			
	MBRD5200			
SPQ	2,500pcs/Reel			
AiT provides all RoHS Compliant Products				

### **PIN DESCRIPTION**



Pin#	Description
1	Anode
2	Cathode
3	Anode
4	Cathode

#### MBRD540\_MBRD5200 SCHOTTKY DIODE 5.0A SCHOTTKY BARRIER RECTIFIER

# **ABSOLUTE MAXIMUM RATINGS**

T<sub>A</sub> = 25°C, unless otherwise specified.

Parameter	Symbols	MBRD540	MBRD545	MBRD560	Units
Maximum Recurrent Peak Reverse	V <sub>RRM</sub>	40	45	60	V
Voltage					
Maximum RMS voltage	V <sub>RMS</sub>	28	31.5	42	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	40	45	60	V
Maximum Average Forward Rectified	1				Α
Current	I <sub>F(AV)</sub>		5.0		
Peak Forward Surge Current,8.3ms Single	1	I <sub>FSM</sub> 150			А
Half Sine-wave Super imposed on Rated	IFSM				
Load (JEDEC method)					
Maximum Forward Voltage at 5.0A DC	VF	0.60 0.70		0.70	V
Maximum DC Reverse Current J= 25°C	1-	0.5			- A
at Rated DC Blocking Voltage J =125°C	I <sub>R</sub>	20			mA
Typical Junction Capacitance Per	C	600	1	400	
Element <sup>(1)</sup>	C <sub>j</sub>	600		400	pF
Typical Thermal Resistance (2)	RθJA	35		°C/W	
Operating Temperature Range	Tj	-55 to +150		°C	
Storage Temperature Range	T <sub>stg</sub>	-55 to +150		°C	

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

- (1) Measured at 1.0MHz and applied reverse voltage of 4.0 V D.C.
- (2) Mounted on 10cm x 10cm x 1mm copper pad area

#### MBRD540\_MBRD5200 SCHOTTKY DIODE 5.0A SCHOTTKY BARRIER RECTIFIER

Parameter	Symbols	MBRD5100	MBRD5150	MBRD5200	Units
Maximum Recurrent Peak Reverse	V <sub>RRM</sub>	100	150	200	V
Voltage					
Maximum RMS voltage	$V_{RMS}$	70	105	140	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	100	150	200	V
Maximum Average Forward Rectified Current	I <sub>F(AV)</sub>	5.0			А
Peak Forward Surge Current,8.3ms Single Half Sine-wave Super imposed on Rated Load (JEDEC method)	Iғsм	150			А
Maximum Forward Voltage at 5.0A DC	VF	0.85	0.90	0.92	V
Maximum DC Reverse Current J= 25°C at Rated DC Blocking Voltage J =125°C	I <sub>R</sub>	0.5 20			mA
Typical Junction Capacitance Per Element <sup>(1)</sup>	C <sub>j</sub>	400			pF
Typical Thermal Resistance (2)	Reja	35			°C/W
Operating Temperature Range	Tj	-55 to +150			°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150			°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>(1)</sup>Measured at 1.0MHz and applied reverse voltage of 4.0 V D.C.

<sup>(2)</sup>Mounted on 10cm x 10cm x 1mm copper pad area

# MBRD540\_MBRD5200

SCHOTTKY DIODE 5.0A SCHOTTKY BARRIER RECTIFIER

#### TYPICAL CHARACTERISTICS

Fig 1. TYPICAL FORWARD CURRENT DERATING CURVE

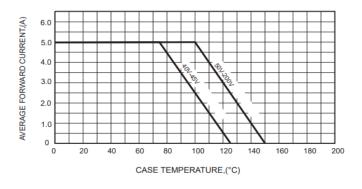


Fig 2. MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

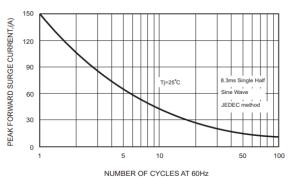


Fig 3. TYPICAL FORWARD CHARACTERISTICS

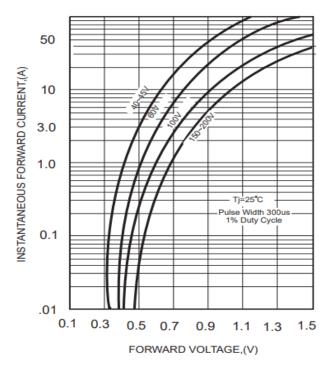
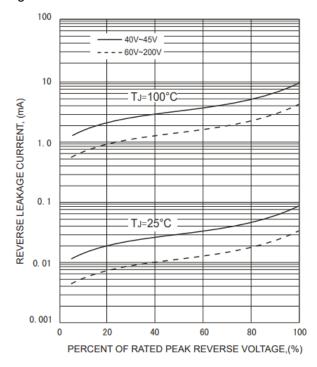


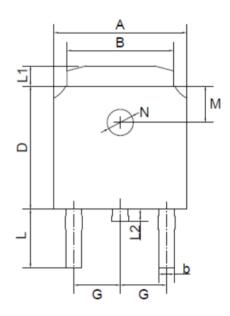
Fig 4. TYPICAL REVERSE CHARACTERISTICS

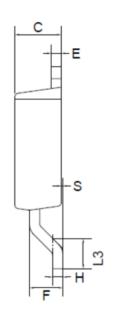


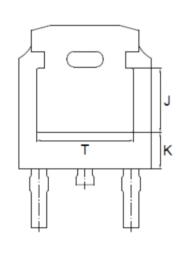
SCHOTTKY DIODE 5.0A SCHOTTKY BARRIER RECTIFIER

# **PACKAGE INFORMATION**

Dimension in TO-252 (Unit: mm)







Symbol	Min	Max	Symbol	Min	Max
А	6.3	6.7	L1	0.8	1.2
В	5.1	5.5	L2	0.6	1.0
b	0.3	0.8	L3	1.40	1.75
С	2.1	2.5	S	0.0	0.1
D	5.9	6.3	М	1.8 TYPICAL	
E	0.4	0.6	N	1.3 TYPICAL	
F	1.3	1.8	J	3.16 ref.	
G	2.29TY	2.29TYPICAL		1.80	ref.
Н	0.45	0.55	L	4.83 ref.	
L	2.7	3.1			

MBRD540\_MBRD5200 SCHOTTKY DIODE 5.0A SCHOTTKY BARRIER RECTIFIER

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